# P-Channel 20-V (D-S) MOSFET

## **Key Features:**

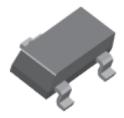
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

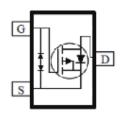
## **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
-20	43 @ V <sub>GS</sub> = -4.5V	-4.5	
	54 @ V <sub>GS</sub> = -2.5V	-4.1	
	120 @ V <sub>GS</sub> = -1.8V	-2.7	









ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage			-20	V	
Gate-Source Voltage			±8		
0	T <sub>A</sub> =25°C		-4.5		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =70°C	l <sub>D</sub>	-3.6	Α	
Pulsed Drain Current <sup>b</sup>	-	I <sub>DM</sub>	-20		
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	-1.8	А	
Decree Distriction 8	T <sub>A</sub> =25°C	В	1.3	W	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	P <sub>D</sub>	0.8	l vv	
Operating Junction and Storage Temperature Range	-	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	100	°C/W		
Maximum Junction-to-Ambient	Steady State	I <b>V</b> OJA	166	C/VV		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# MI2305PE

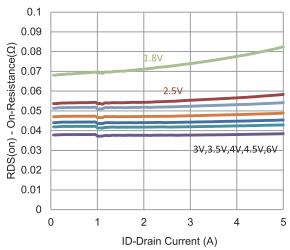
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	uA
Zero Gate Voltage Drain Current	1	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
	DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			Α
		$V_{GS} = -4.5 \text{ V}, I_{D} = -3.7 \text{ A}$			43	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -3 \text{ A}$			54	mΩ
		$V_{GS} = -1.8 \text{ V}, _{I}D = -2.4 \text{ A}$			120	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -3.7 \text{ A}$		15		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -0.9 \text{ A}, V_{GS} = 0 \text{ V}$		-0.73		V
		Dynamic <sup>b</sup>				
Total Gate Charge	$Q_g$	$Q_g$ $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_D = -3.7 \text{ A}$		11		]
Gate-Source Charge	$Q_gs$			2.1		nC
Gate-Drain Charge	$Q_gd$	ID 0.7 7.		2.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = -10 \text{ V}, R_1 = 2.8 \Omega,$		10		
Rise Time	t <sub>r</sub>	$I_{DS} = -10 \text{ V}, 11 = 2.0 \Omega,$		11		ns
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		56		
Fall Time	t <sub>f</sub>	V GEN 1.0 V, I GEN 0 12		20		
Input Capacitance	C <sub>iss</sub>			697		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		80		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			70		

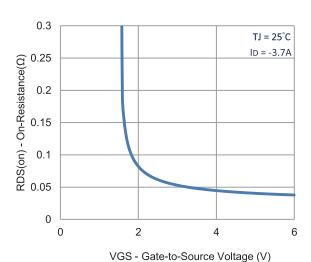
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

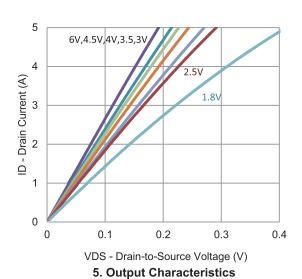
## **Typical Electrical Characteristics**

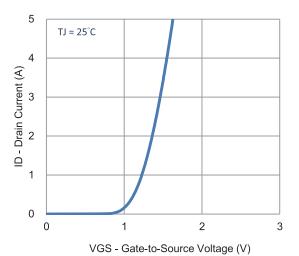


#### 1. On-Resistance vs. Drain Current

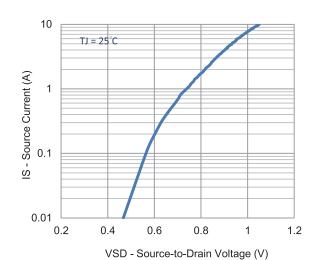


3. On-Resistance vs. Gate-to-Source Voltage

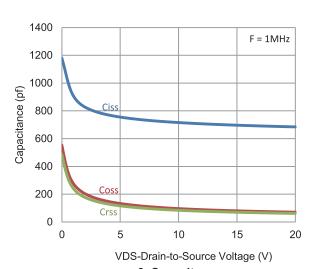




2. Transfer Characteristics

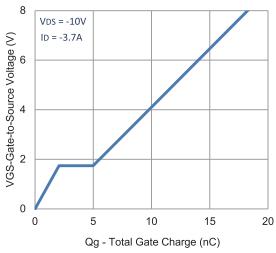


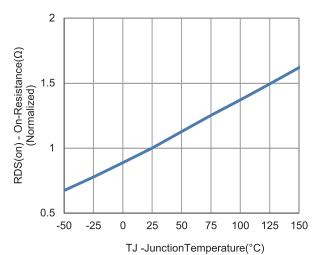
4. Drain-to-Source Forward Voltage



6. Capacitance

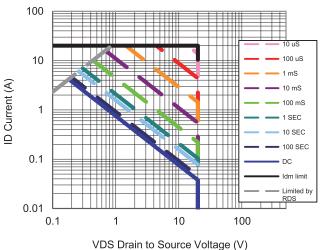


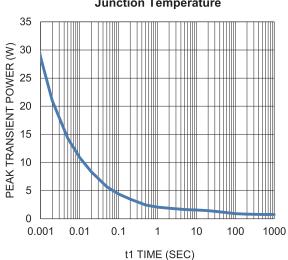




7. Gate Charge

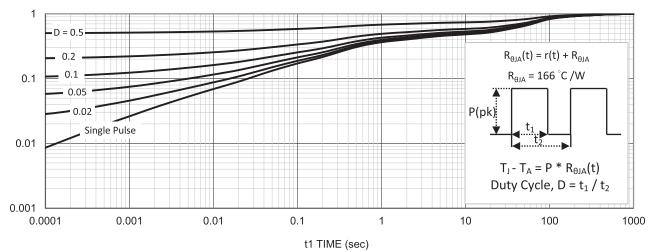






9. Safe Operating Area

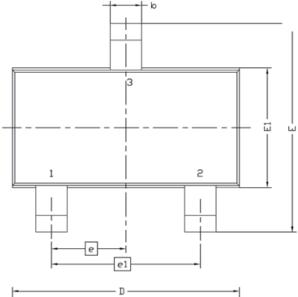
10. Single Pulse Maximum Power Dissipation



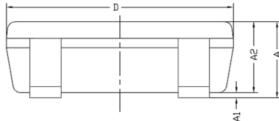
11. Normalized Thermal Transient Junction to Ambient

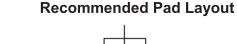
Analog Power SOT-23

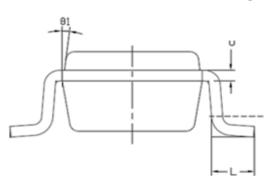
## **Package Information**

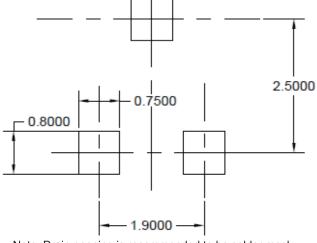


Symbol	MILLIMETERS		
Syllibol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
Е	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		









Note: Drain opening is recommended to be solder mask defined in a copper fill for improved thermal performance

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